

DUAL PRE-BIASED TRANSISTORS FOR POWER MANAGEMENT

Features

- **Epitaxial Planar Die Construction**
- **Built-In Biasing Resistors**
- One 500mA PNP and One 100mA NPN
- Lead Free/RoHS Compliant (Note 1)
- "Green" Device (Note 3 and 4)

Mechanical Data

- Case: SOT-363
- Case Material Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020A
- Terminals: Finish Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Marking Code: C73 See Page 4
- Ordering & Date Code: See Page 4
- Terminal Connections: See Diagram
- Weight: 0.015 grams (approximate)

∱ J	
	T ₁₂ R ₁ R ₂

Dim Min Max Α 0.10 0.30 В 1.15 1.35 С 2.00 2.20 D 0.65 Nominal 0.30 0.40 Н 1.80 2.20 J 0.10 Κ 0.90 1.00 L 0.25 0.40 М 0.10 0.25 All Dimensions in mm

SOT-363

T _{r2}	R ₁	R ₂
	ξR ₁	Tr1
		U

В

SCHEMATIC DIAGRAM

P/N		R1	R2
MIMD10A	Tr1	0.1K	10K
	Tr2	10K	-

Maximum Ratings PNP Section Tr1

@TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage	Vcc	-50	V
Input Voltage	V _{IN}	-5 to +5	V
Output Current	Io	-500	mA

Maximum Ratings NPN Section Tr2 @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	lc	100	mA

Maximum Ratings - Total @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 2)	P_d	200	mW
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- 2. Mounted on FR4 PC Board with recommended pad layout at http://www.diodes.com/datasheets/ap02001.pdf.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.



Electrical Characteristics PNP Section Tr1 @TA = 25°C unless otherwise specified

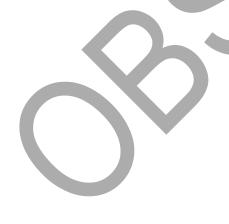
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Input Voltage	$V_{I(off)}$	-0.3			V	$V_{CC} = -5V$, $I_{O} = -100\mu A$
input voitage	V _{I(on)}	_	_	-1.5		V _O = 0.3, I _O = -100mA
Output Voltage	V _{O(on)}	_	-0.1	-0.3	V	I _O = -100mA/-5mA
Input Current	lı	_	_	-25	mA	V _I = -2V
Output Current	I _{O(off)}	_	_	-0.5	μА	V _{CC} = -50V, V _I = 0V
DC Current Gain	G _l	68	_	_	_	_
Gain-Bandwidth Product*	f⊤	_	200	_	MHz	V _{CE} = -10V, I _E = -50mA, f = 100MHz

^{*} Transistor - For Reference Only

Electrical Characteristics NPN Section Tr2 @T_A = 25°C unless otherwise specified

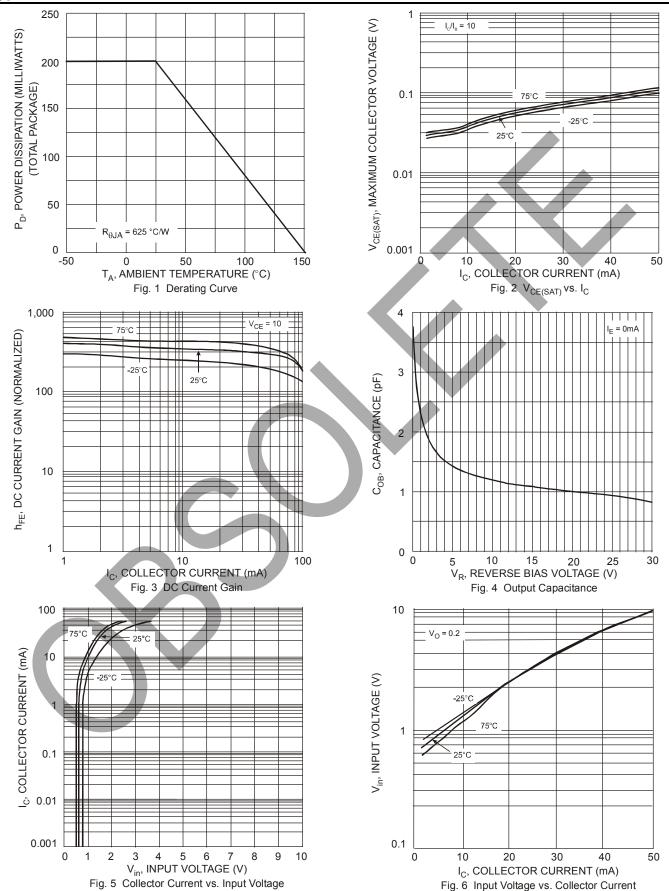
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
- That dotorious	Cynnoc.		. , , ,	Max	O	1 det demantion
Collector-Base Breakdown Voltage	BV_CBO	50	_	_	V	I _C = 50μA
Collector-Emitter Breakdown Voltage	BV _{CEO}	50	_	_	V	I _C = 1mA
Emitter-Base Breakdown Voltage	BV _{EBO}	5	_	_	V	I _E = 50μA
Collector Cutoff Current	I _{CBO}	_	_	0.5	μΑ	V _{CB} = 50V
Emitter Cutoff Current	I _{EBO}	_	_	0.5	μА	V _{EB} = 4V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	_	0.3	V	I _C /I _B = 10mA / 1.0mA
DC Current Transfer Ratio	h _{FE}	100	250	600	_	I _C = 1mA, V _{CE} = 5V
Gain-Bandwidth Product*	f _T	_	250	_	MHz	V _{CE} = 10V, I _E = -5mA, f = 100MHz

^{*} Transistor - For Reference Only





Typical Curves - Tr2



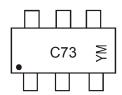


Ordering Information (Note 5)

Device	Packaging	Shipping
MIMD10A-7-F	SOT-363	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



C73 = Product Type Marking Code YM = Date Code Marking Y = Year ex: P = 2003 M = Month ex: 9 = September

Date Code Key

Year	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	Р	R	S	T	J	V	W	Х	Υ	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D





IMPORTANT NOTICE

- 1. DIODES INCORPORATED AND ITS SUBSIDIARIES ("DIODES") MAKE NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO ANY INFORMATION CONTAINED IN THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).
- 2. The Information contained herein is for informational purpose only and is provided only to illustrate the operation of Diodes products described herein and application examples. Diodes does not assume any liability arising out of the application or use of this document or any product described herein. This document is intended for skilled and technically trained engineering customers and users who design with Diodes products. Diodes products may be used to facilitate safety-related applications; however, in all instances customers and users are responsible for (a) selecting the appropriate Diodes products for their applications, (b) evaluating the suitability of the Diodes products for their intended applications, (c) ensuring their applications, which incorporate Diodes products, comply the applicable legal and regulatory requirements as well as safety and functional-safety related standards, and (d) ensuring they design with appropriate safeguards (including testing, validation, quality control techniques, redundancy, malfunction prevention, and appropriate treatment for aging degradation) to minimize the risks associated with their applications.
- 3. Diodes assumes no liability for any application-related information, support, assistance or feedback that may be provided by Diodes from time to time. Any customer or user of this document or products described herein will assume all risks and liabilities associated with such use, and will hold Diodes and all companies whose products are represented herein or on Diodes' websites, harmless against all damages and liabilities.
- 4. Products described herein may be covered by one or more United States, international or foreign patents and pending patent applications. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks and trademark applications. Diodes does not convey any license under any of its intellectual property rights or the rights of any third parties (including third parties whose products and services may be described in this document or on Diodes' website) under this document.
- 5. Diodes products are provided subject to Diodes' Standard Terms and Conditions of Sale (https://www.diodes.com/about/company/terms-and-conditions/terms-and-conditions-of-sales/) or other applicable terms. This document does not alter or expand the applicable warranties provided by Diodes. Diodes does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.
- 6. Diodes products and technology may not be used for or incorporated into any products or systems whose manufacture, use or sale is prohibited under any applicable laws and regulations. Should customers or users use Diodes products in contravention of any applicable laws or regulations, or for any unintended or unauthorized application, customers and users will (a) be solely responsible for any damages, losses or penalties arising in connection therewith or as a result thereof, and (b) indemnify and hold Diodes and its representatives and agents harmless against any and all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim relating to any noncompliance with the applicable laws and regulations, as well as any unintended or unauthorized application.
- 7. While efforts have been made to ensure the information contained in this document is accurate, complete and current, it may contain technical inaccuracies, omissions and typographical errors. Diodes does not warrant that information contained in this document is error-free and Diodes is under no obligation to update or otherwise correct this information. Notwithstanding the foregoing, Diodes reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes.
- 8. Any unauthorized copying, modification, distribution, transmission, display or other use of this document (or any portion hereof) is prohibited. Diodes assumes no responsibility for any losses incurred by the customers or users or any third parties arising from any such unauthorized use.

Copyright © 2021 Diodes Incorporated

www.diodes.com

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - Pre-Biased category:

Click to view products by Diodes Incorporated manufacturer:

Other Similar products are found below:

RN1607(TE85L,F) DTA124GKAT146 DTA144WETL DTA144WKAT146 DTC113EETIG DTC115TETL DTC115TKAT146

DTC124TETL DTC144ECA-TP DTC144VUAT106 MUN5241T1G NSBA114TDP6T5G NSBA143ZF3T5G NSBC114YF3T5G

NSBC123TF3T5G SMUN5330DW1T1G SSVMUN5312DW1T2G RN1303(TE85L,F) RN4605(TE85L,F) TTEPROTOTYPE79

DDTC114EUAQ-7-F EMH15T2R SMUN2214T3G NSBC114TF3T5G NSBC143ZPDP6T5G NSVMUN5113DW1T3G

SMUN5230DW1T1G SMUN5133T1G SMUN2214T1G DTC114EUA-TP NSBA144EF3T5G NSVDTA114EET1G 2SC2223-T1B-A

2SC3912-TB-E SMUN5237DW1T1G SMUN5213DW1T1G SMUN5114DW1T1G SMUN2111T1G NSVDTC144EM3T5G DTC124ECA-TP DTC123TM3T5G DTA114ECA-TP DTA113EM3T5G DCX115EK-7-F DTC113EM3T5G NSVMUN5135DW1T1G

NSVDTC143ZM3T5G SMUN5216DW1T1G NSVMUN5312DW1T2G NSVMUN5215DW1T1G